

NCE N-Channel Super Trench II Power MOSFET

Description

The NCEP038N10GU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

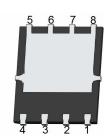
General Features

- $V_{DS} = 100V, I_{D} = 135A$
 - $R_{DS(ON)}$ =3.45m Ω (Typ.) @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

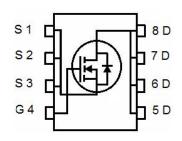
DFN 5X6





Top View

Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P038N10GU	NCEP038N10GU	DFN5X6-8L	Ø330mm	12 mm	5000 units

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	135	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	108	Α
Pulsed Drain Current ^(Note 1)	I _{DM}	540	Α
Maximum Power Dissipation	P _D	170	W
Derating factor		1.36	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	750	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	Rejc	0.74	°C/W

NCEP038N10GU

Electrical Characteristics (T_C=25°Cunless otherwise noted)

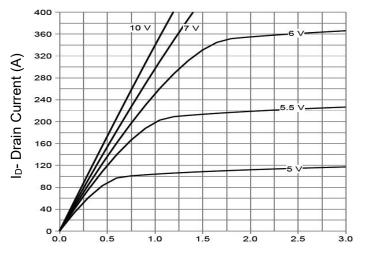
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =67.5A	-	3.45	3.8	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =67.5A		130	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	6300	-	PF
Output Capacitance	Coss	$V_{DS}=50V, V_{GS}=0V,$	-	560	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz - 40 -	-	PF		
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	23	-	nS
Turn-on Rise Time	t _r	V_{DD} =50 V , I_{D} =67.5 A ,	-	15	-	nS
Turn-Off Delay Time	t _{d(off)}	$V_{\text{GS}}\text{=}10V, R_{\text{G}}\text{=}3\Omega$	-	48	-	nS
Turn-Off Fall Time	t _f		-	16	-	nS
Total Gate Charge	Qg	\/ 50\/ 07.54	-	110	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =50V,I _D =67.5A,	-	33		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	30		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =67.5A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	135	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =67.5A	-	70	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	117	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

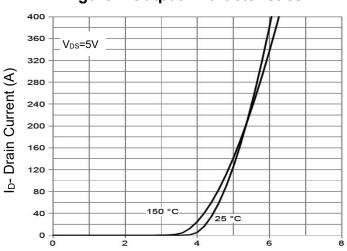


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

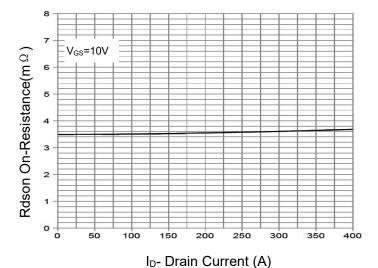
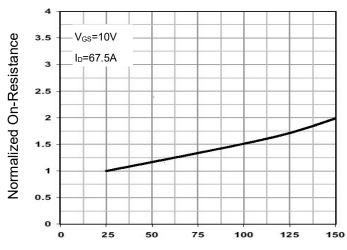
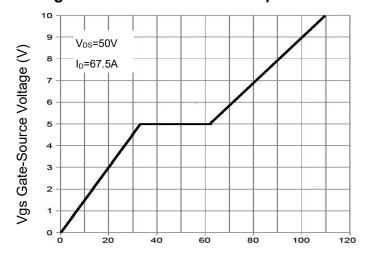


Figure 3 Rdson- Drain Current

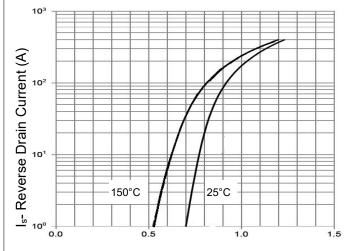


T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



Qg Gate Charge (nC)
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



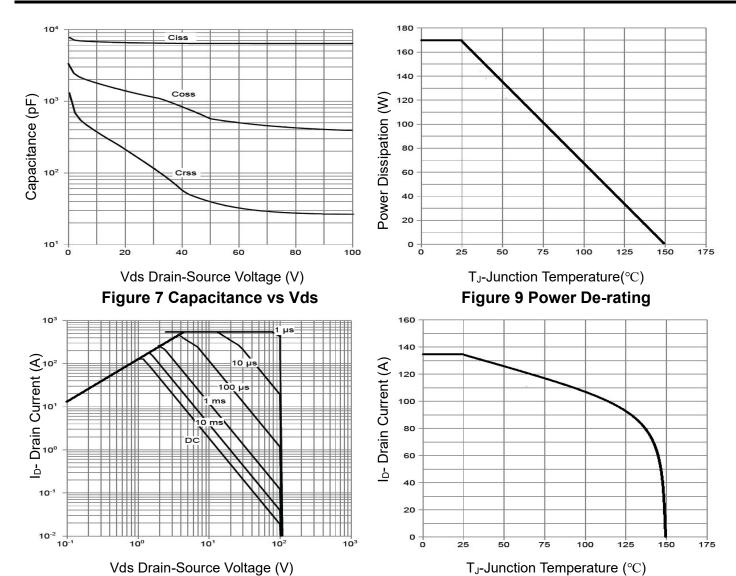


Figure 8 Safe Operation Area

Figure 10 Current De-rating

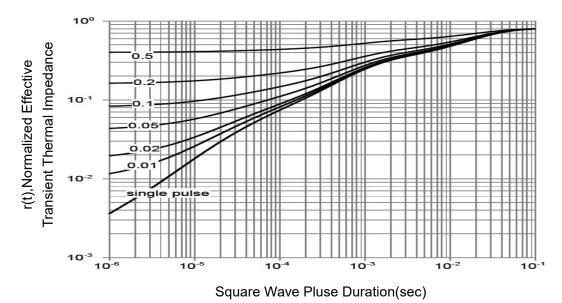
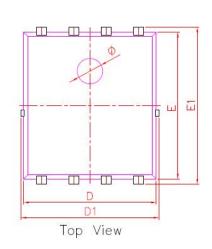
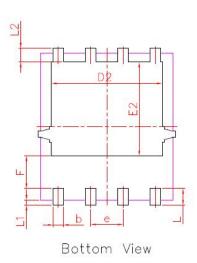


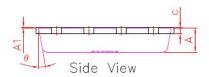
Figure 11 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L (E) Package Information



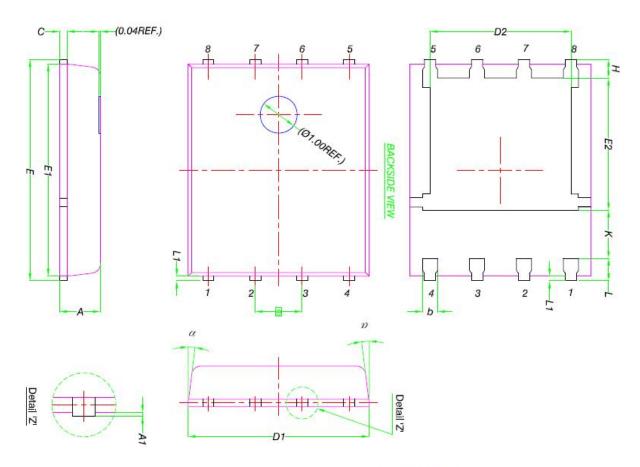




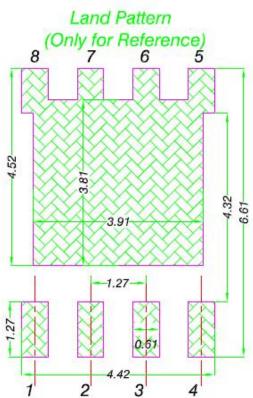
DIM.	MIN.	NOM.	MAX.
Α	0.90	0.95	1.00
A1	0.00	0.02	0.05
b	0.35	0.40	0.50
С	0.20	0.25	0.30
D	5.10	5.20	5.30
D1	5.10	5.40	5.50
D2	4.25	4.35	4.45
е		1.27 BSC	
Е	5.70	5.75	5.80
E1	6.00	6.15	6.30
E2	3.57	3.67	3.77
F	1.18	1.28	1.38
L	0.55	0.65	0.75
L1	0.15	0.20	0.25
L2	0.45	0.55	0.65
Ø	0.90	1.00	1.10
Θ	8°	10°	12°



DFN5X6-8L (G) Package Information



02000	N	ILLIMETI	ERS
DIM.	MIN.	NOM.	MAX.
Α	0.90	1.00	1.10
A1	0	6	0.05
b	0.33	0.41	0.51
С	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
Ε	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
е	1	1.27 BSC	
Н	0.41	0.51	0.61
K	1.10	((*)	36
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	1.5	12°



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NCEP038N10GU

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